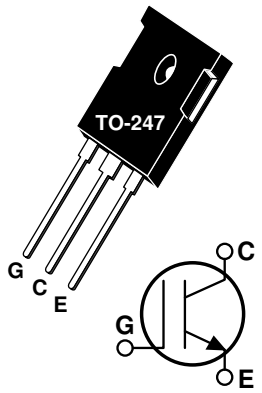
APT33GF120BR(G)

*G Denotes RoHS Compliant, Pb Free Terminal Finish.

1200V 52A

The Fast IGBT is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Fast IGBT offers superior ruggedness, fast switching speed and low Collector-Emitter On voltage.

- **Low Forward Voltage Drop**
- **Ultra Low Leakage Current**
- **Low Tail Current**
- **RBSOA and SCSOA Rated**
- **High Freq. Switching to 20KHz**



MAXIMUM RATINGS (IGBT) All Ratings: T_C = 25°C unless otherwise specified.

Symbol	Parameter	APT33GF120BR(G)	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{CGR}	Collector-Gate Voltage (R_{GE} = 20KΩ)	1200	
V_{GE}	Gate Emitter Voltage	±20	
I_{C1}	Continuous Collector Current @ T_C = 25°C	52	Amps
I_{C2}	Continuous Collector Current @ T_C = 105°C	33	
I_{CM}	Pulsed Collector Current ① @ T_C = 25°C	104	
I_{LM}	RBSOA Clamped Inductive Load Current @ R_G = 11Ω T_C = 125 °C	66	
E_{AS}	Single Pule Avalanche Energy②	65	mJ
P_D	Total Power Dissipation	297	Watts
T_J,T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS (IGBT)

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage (V_{GE} = 0V, I_C = 0.5mA)	1200			Volts
$V_{GE}(TH)$	Gate Threshold Voltage (V_{CE} = V_{GE}, I_C = 700µA, T_j = 25°C)	4.5	5.5	6.5	
$V_{CE}(ON)$	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 25A, T_j = 25°C)		2.7	3.2	
	Collector-Emitter On Voltage (V_{GE} = 15V, I_C = 25A, T_j = 125°C)		3.3	3.9	
I_{CES}	Collector Cut-off Current (V_{CE} = V_{CES}, V_{GE} = 0V, T_j = 25°C)			0.5	mA
	Collector Cut-off Current (V_{CE} = V_{CES}, V_{GE} = 0V, T_j = 125°C)			5.0	
I_{GES}	Gate-Emitter Leakage Current (V_{GE} = ±20V, V_{CE} = 0V)			±100	nA

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - http://www.advancedpower.com

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DYNAMIC CHARACTERISTICS (IGBT)

APT33GF120BR(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	**Capacitance** V_{GE} = 0V, V_{CE} = 25V, f = 1 MHz		1855		pF
C_{oes}	Output Capacitance			230		
C_{res}	Reverse Transfer Capacitance			110		
Q_g	Total Gate Charge ③	**Gate Charge** V_{GE} = 15V, V_{CC} = 0.5V_{CES}, I_C = I_{C2}		170		nC
Q_{ge}	Gate-Emitter Charge			19		
Q_{gc}	Gate-Collector ("Miller") Charge			100		
$t_d(on)$	Turn-on Delay Time	**Resistive Switching (25°C)** V_{GE} = 15V, V_{CC} = 0.8V_{CES}, I_C = I_{C2}, R_G =10Ω		24		ns
t_r	Rise Time			85		
$t_d(off)$	Turn-off Delay Time			170		
t_f	Fall Time			125		
$t_d(on)$	Turn-on Delay Time	**Inductive Switching (150°C)** V_{CLAMP}(Peak) = 0.66V_{CES}, V_{GE} = 15V, I_C = I_{C2}, R_G = 10Ω, T_J = +150°C		25		ns
t_r	Rise Time			60		
$t_d(off)$	Turn-off Delay Time			210		
t_f	Fall Time			74		
E_{on}	Turn-on Switching Energy			2.8		mJ
E_{off}	Turn-off Switching Energy			2.8		
E_{ts}	Total Switching Losses			5.6		
$t_d(on)$	Turn-on Delay Time	**Inductive Switching (25°C)** V_{CLAMP}(Peak) = 0.66V_{CES}, V_{GE} = 15V, I_C = I_{C2}, R_G = 10Ω, T_J = +25°C		27		ns
t_r	Rise Time			65		
$t_d(off)$	Turn-off Delay Time			190		
t_f	Fall Time			70		
E_{ts}	Total Switching Losses			5.2		mJ
gfe	Forward Transconductance	V_{CE} = 20V, I_C = 25A	8.5	20		S

THERMAL AND MECHANICAL CHARACTERISTICS (IGBT and FRED)

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\Theta JC}$	Junction to Case			0.42	°C/W
$R_{\Theta JA}$	Junction to Ambient			40	
W_T	Package Weight		0.22		oz
			5.90		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② I_C = I_{C2}, V_{CC} = 50V, R_{GE} = 25Ω, L = 120µH, T_j = 25°C

③ See MIL-STD-750 Method 3471

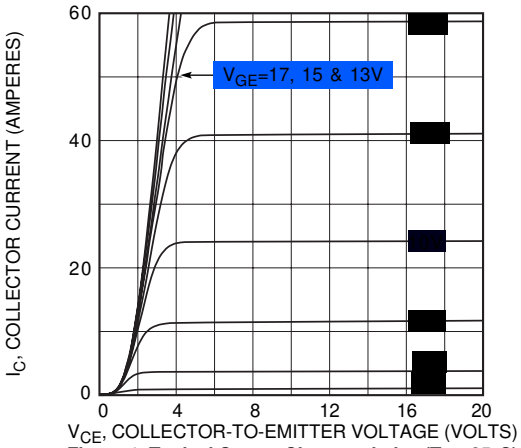


Figure 1, Typical Output Characteristics (T_J = 25°C)

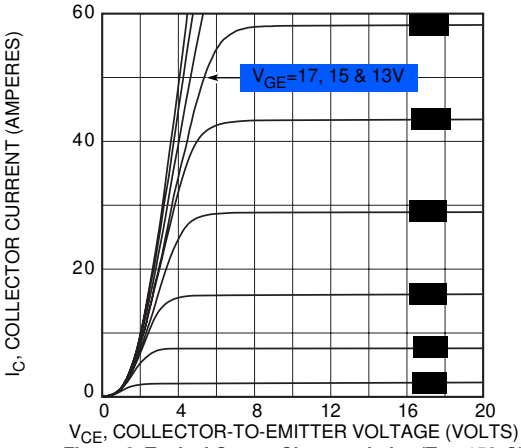


Figure 2, Typical Output Characteristics (T_J = 150°C)

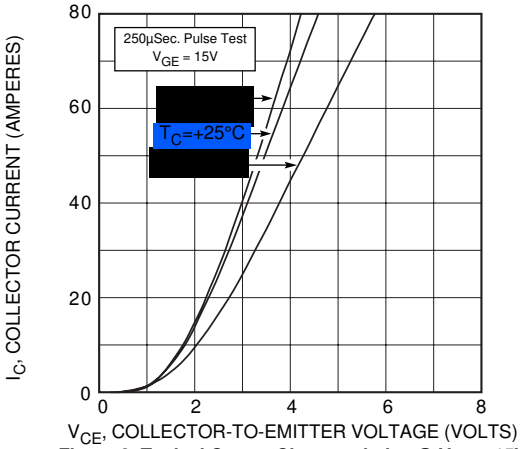


Figure 3, Typical Output Characteristics @ V_{GE} = 15V

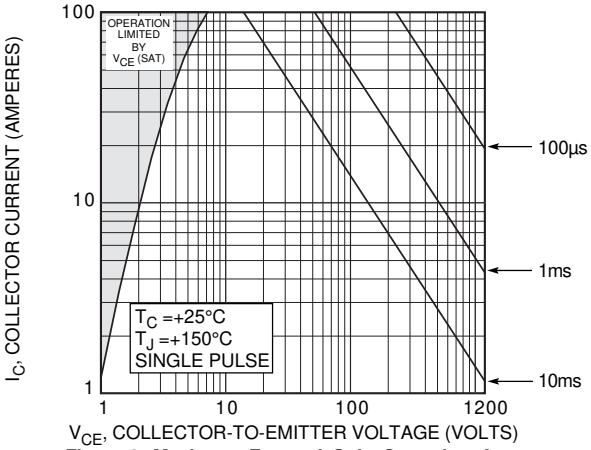


Figure 4, Maximum Forward Safe Operating Area

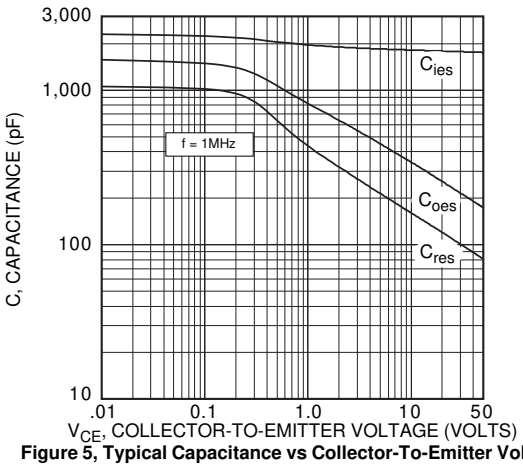


Figure 5, Typical Capacitance vs Collector-To-Emitter Voltage

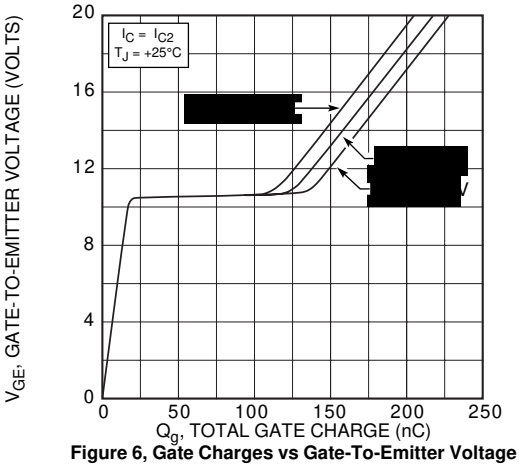


Figure 6, Gate Charges vs Gate-To-Emitter Voltage

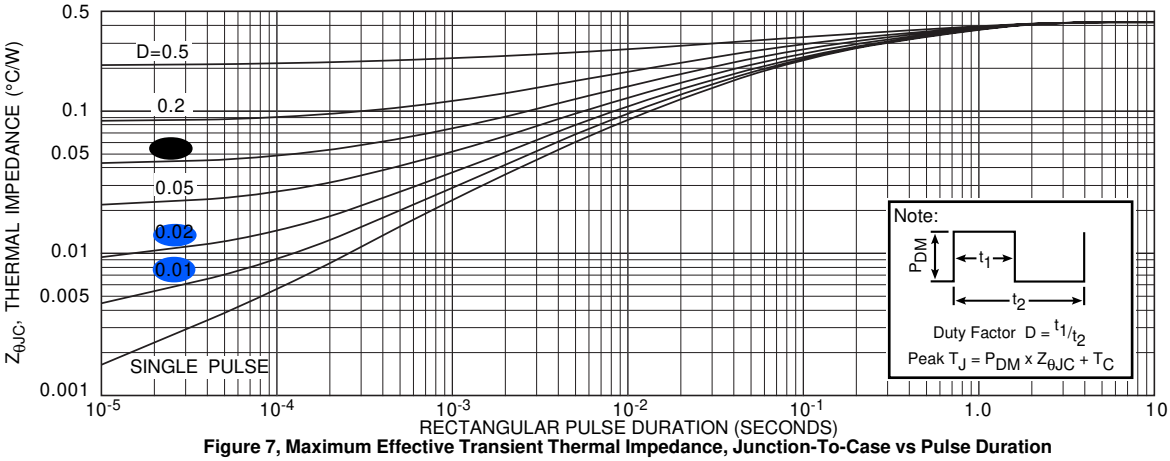


Figure 7, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

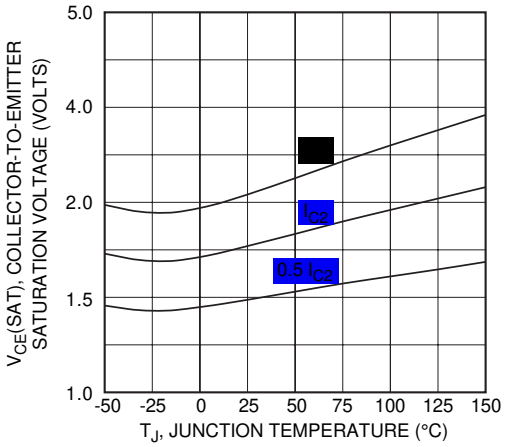


Figure 8, Typical V_{CE}(SAT) Voltage vs Junction Temperature

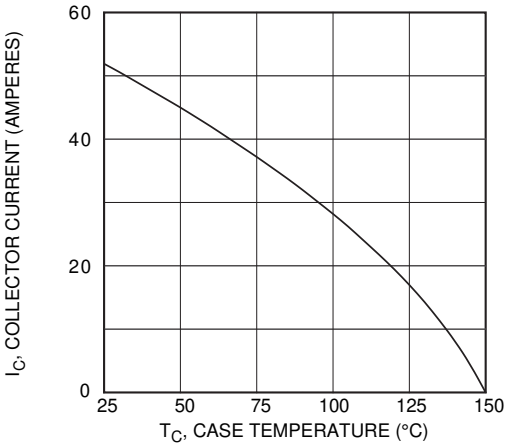


Figure 9, Maximum Collector Current vs Case Temperature

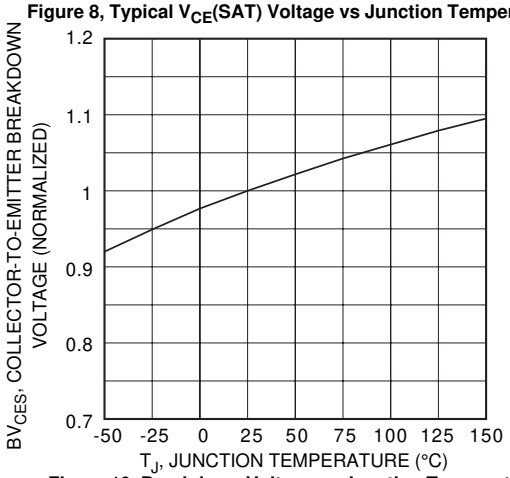


Figure 10, Breakdown Voltage vs Junction Temperature

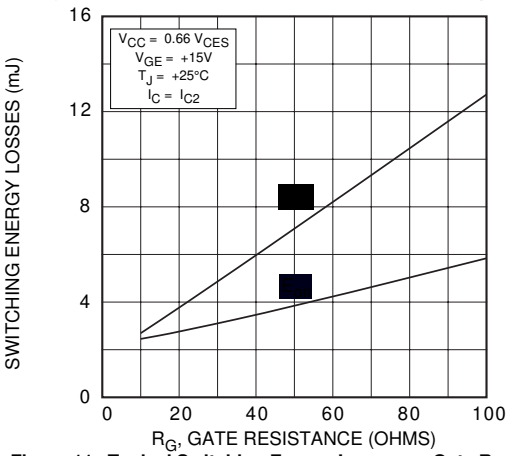


Figure 11, Typical Switching Energy Losses vs Gate Resistance

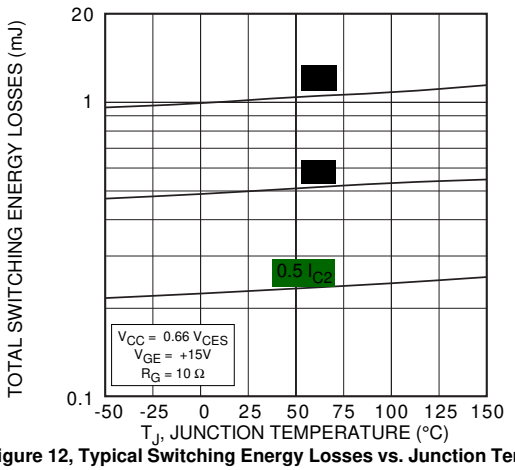


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

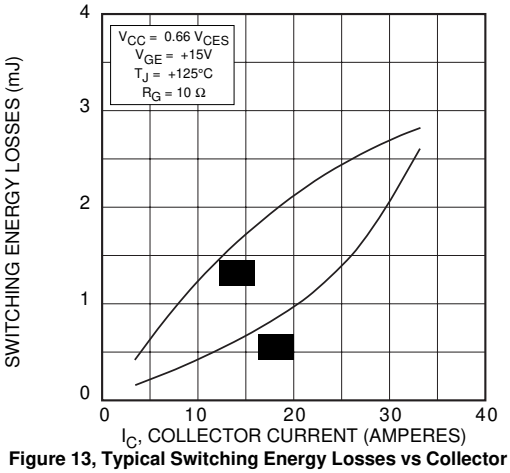


Figure 13, Typical Switching Energy Losses vs Collector Current

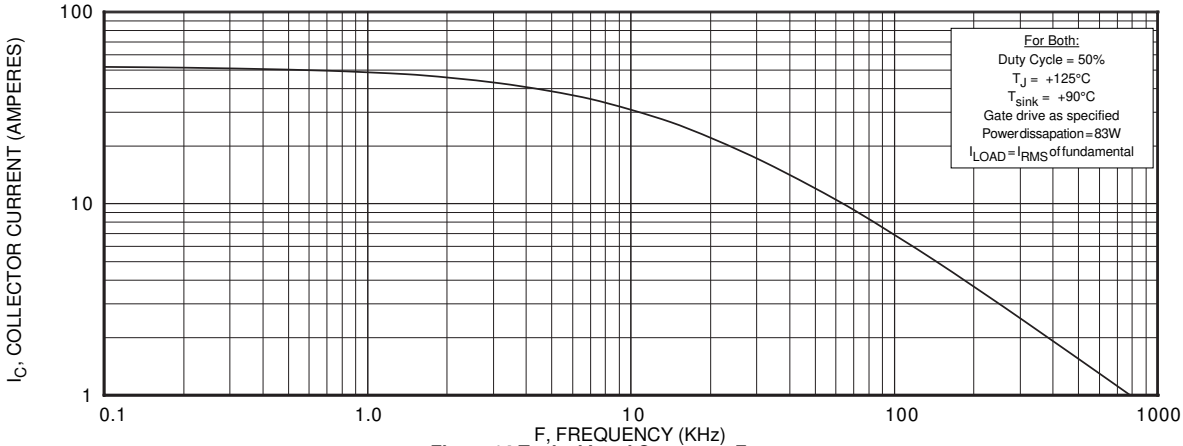


Figure 14,Typical Load Current vs Frequency

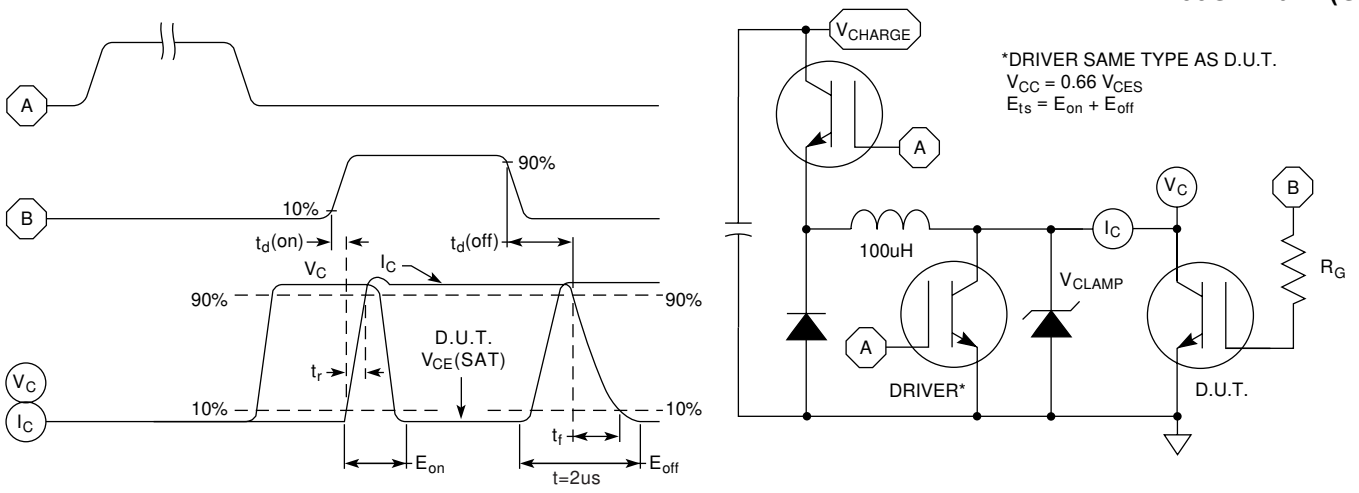


Figure 15, Switching Loss Test Circuit and Waveforms

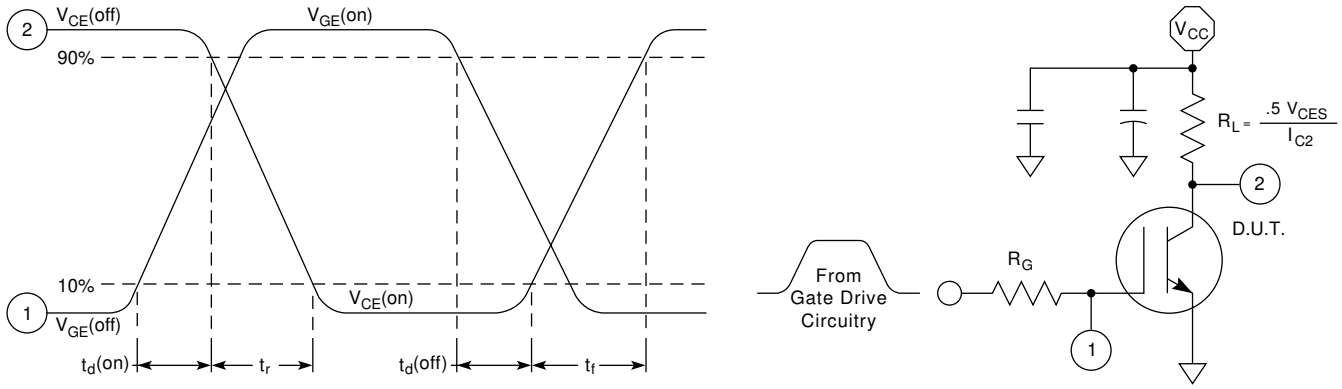
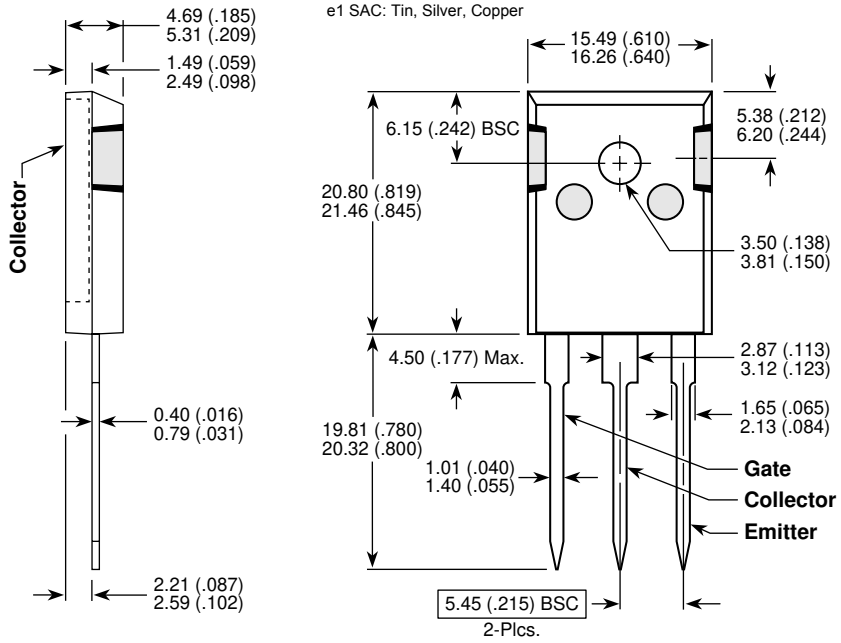


Figure 16, Resistive Switching Time Test Circuit and Waveforms

T0-247 Package Outline



Dimensions in Millimeters and (Inches)